

FUKUCOM COMPANY LTD.

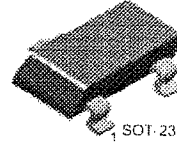
福 靈 有 限 公 司

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S9015S

Low Frequency, Low Noise Amplifier

*Complement to S9014S



1. Base 2. Emitter 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-100	mA
P_C	Collector Dissipation	225	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55~150	$^\circ\text{C}$

Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C=-100\mu\text{A}, I_E=0$	-50			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C=-1\text{mA}, I_B=0$	-45			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E=-100\mu\text{A}, I_C=0$	-5			V
I_{EBO}	Emitter Cut-off Current	$V_{CB}=-50\text{V}, I_E=0$			-50	ηA
I_{CBO}	Collector Cut-off Current	$V_{CE}=-5\text{V}, I_C=0$			-50	ηA
h_{FE}	DC Current Gain	$V_{CE}=-5\text{V}, I_C=-1\text{mA}$	60	200	600	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=-100\text{mA}, I_B=-5\text{mA}$		-0.20	-0.7	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=-100\text{mA}, I_B=-5\text{mA}$		-0.82	-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE}=-5\text{V}, I_C=-2\text{mA}$	-0.6	-0.67	-0.75	V
C_{ob}	Output Capacitance	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		4.5	7	pF
f_T	Current Gain-Bandwidth Product	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$	100	190		MHz
N_F	Noise Figure	$V_{CE}=-5\text{V}, I_C=-0.2\text{mA},$ $F=1\text{KHz}, R_s=1\text{Kohm}$		0.7	10	dB

Classification h_{FE}

h_{FE}	250-480
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Marking

